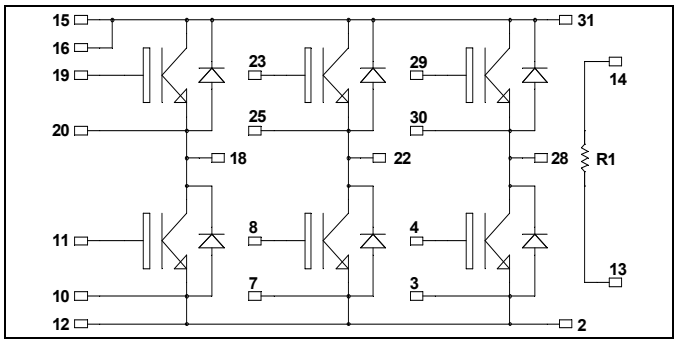
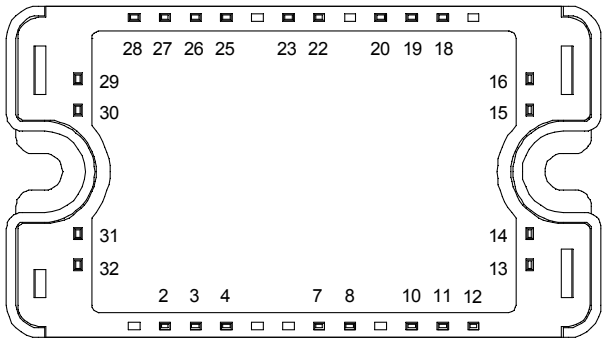
APTGF50X60T3G

3 Phase bridge
NPT IGBT Power Module

V_{CES} = 600V
I_C = 50A* @ Tc = 80°C



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12.
Pins 15 & 16 must be shorted together.



Application

- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	65	A
		T_C = 80°C	50 *	
I_{CM}	Pulsed Collector Current	T_C = 25°C	230	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	250	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	100A @ 500V	

* Specification of IGBT device but output current must be limited to 40A at Tc=80°C not to exceed a connectors temperature greater than 120°C.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V, I_C = 50A	T_j = 25°C	1.7	2.0	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 1mA		4		6	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V, f = 1MHz			2200		pF
C_{oes}	Output Capacitance				323		
C_{res}	Reverse Transfer Capacitance				200		
Q_g	Total gate Charge	V_{GE} = 15V, V_{Bus} = 300V, I_C = 50A			166		nC
Q_{ge}	Gate – Emitter Charge				20		
Q_{gc}	Gate – Collector Charge				100		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V, V_{Bus} = 400V, I_C = 50A, R_G = 2.7Ω			40		ns
T_r	Rise Time				9		
$T_{d(off)}$	Turn-off Delay Time				120		
T_f	Fall Time				12		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V, V_{Bus} = 400V, I_C = 50A, R_G = 2.7Ω			42		ns
T_r	Rise Time				10		
$T_{d(off)}$	Turn-off Delay Time				130		
T_f	Fall Time				21		
E_{on}	Turn-on Switching Energy	V_{GE} = 15V, V_{Bus} = 400V, I_C = 50A, R_G = 2.7Ω	T_j = 125°C		0.5		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		1		

Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			25	µA
			T_j = 125°C			500	
I_F	DC Forward Current		Tc = 80°C		30		A
V_F	Diode Forward Voltage	I_F = 30A			1.8	2.2	V
		I_F = 60A			2.2		
		I_F = 30A	T_j = 125°C		1.5		
t_{rr}	Reverse Recovery Time	I_F = 30A, V_R = 400V, di/dt =200A/µs	T_j = 25°C		25		ns
			T_j = 125°C		160		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		35		nC
			T_j = 125°C		480		

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	*Characteristic*	*Min*	*Typ*	*Max*	*Unit*
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

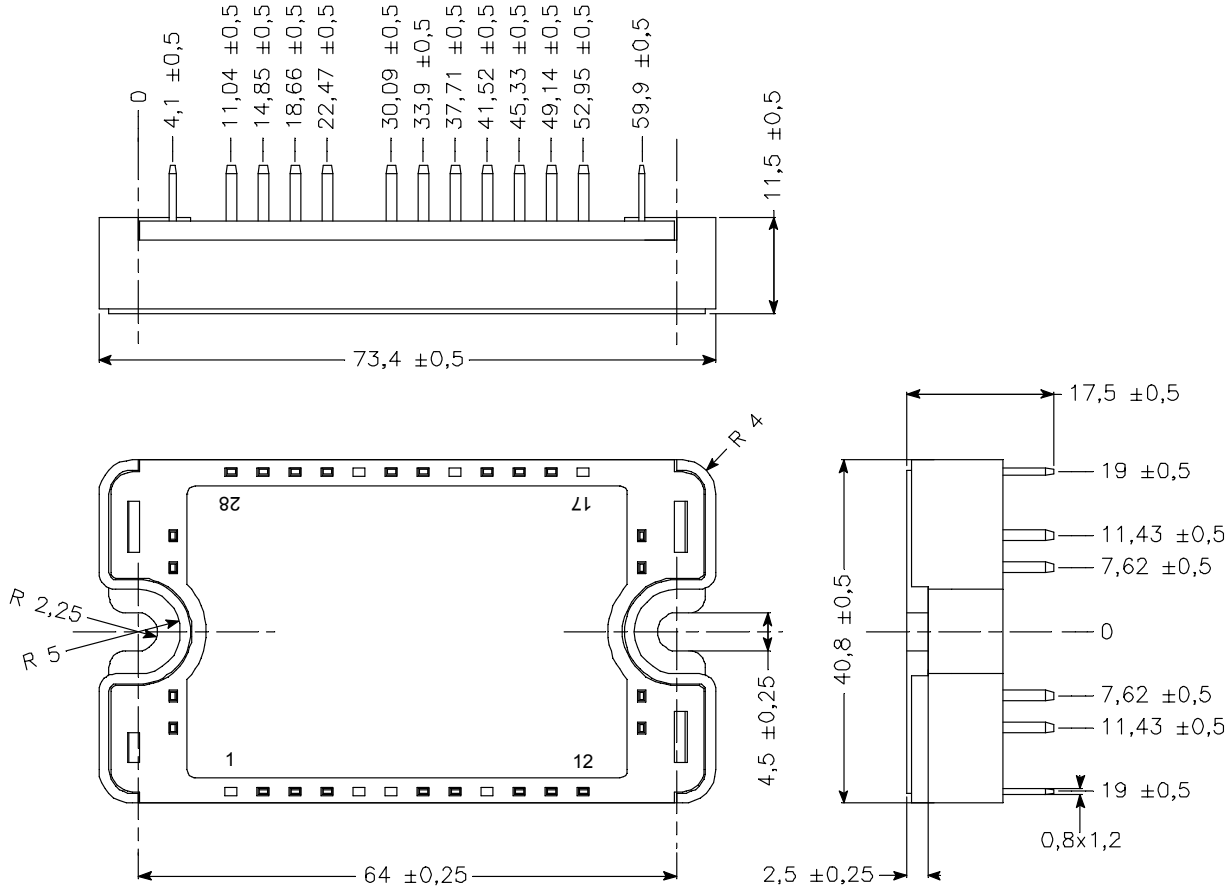
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.5	°C/W
			Diode			1.2	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					110	g

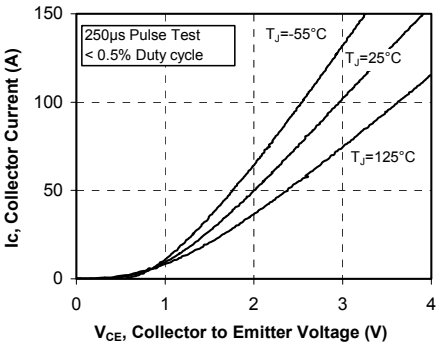
SP3 Package outline (dimensions in mm)



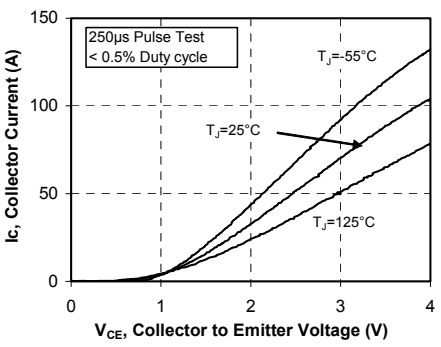
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve

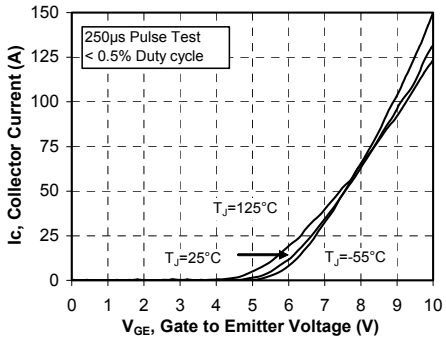
Output characteristics (V_{GE}=15V)



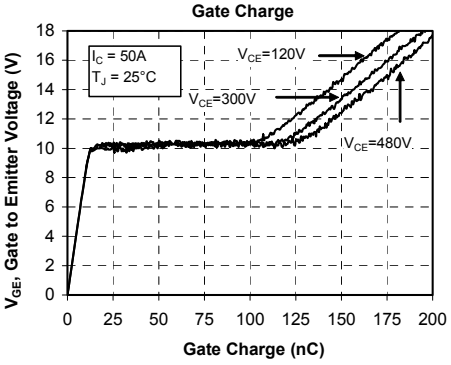
Output Characteristics (V_{GE}=10V)



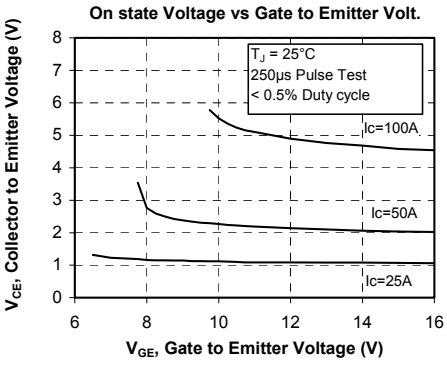
Transfer Characteristics



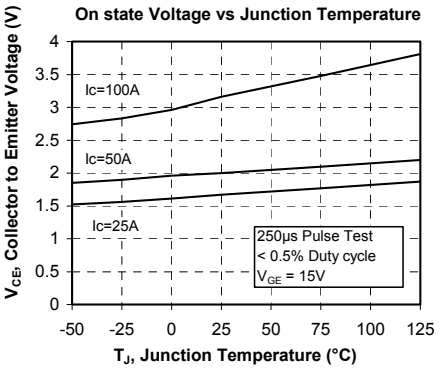
Gate Charge



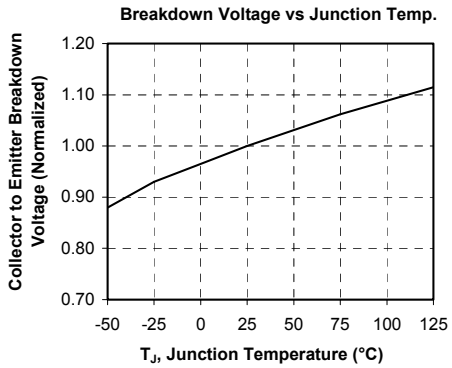
On state Voltage vs Gate to Emitter Volt.



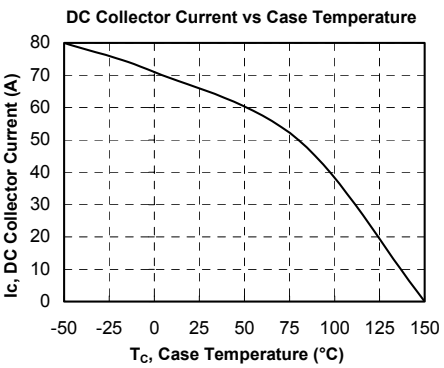
On state Voltage vs Junction Temperature



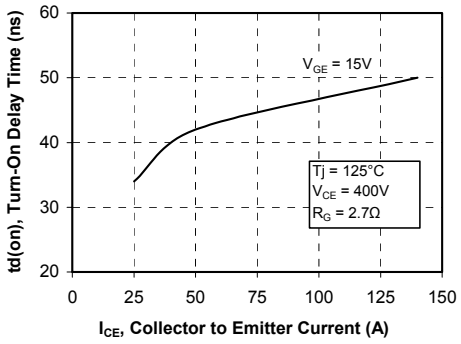
Breakdown Voltage vs Junction Temp.



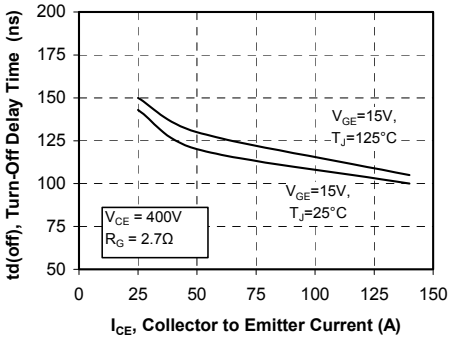
DC Collector Current vs Case Temperature



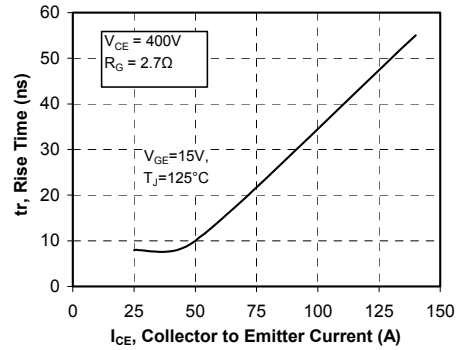
Turn-On Delay Time vs Collector Current



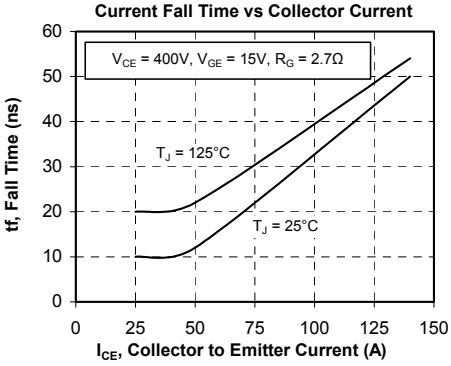
Turn-Off Delay Time vs Collector Current



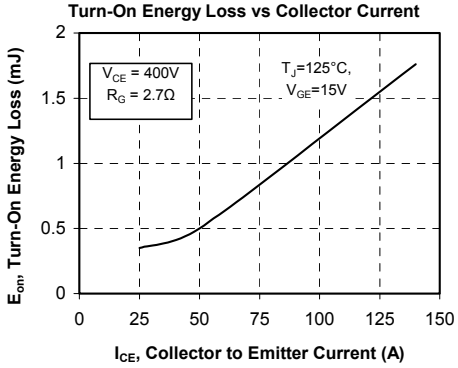
Current Rise Time vs Collector Current



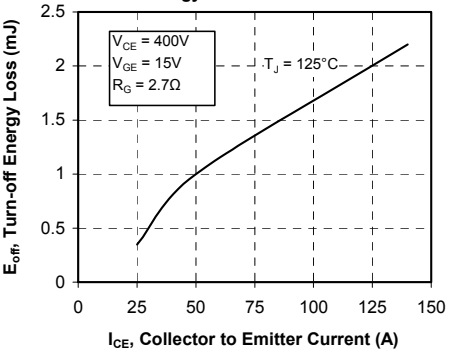
Current Fall Time vs Collector Current



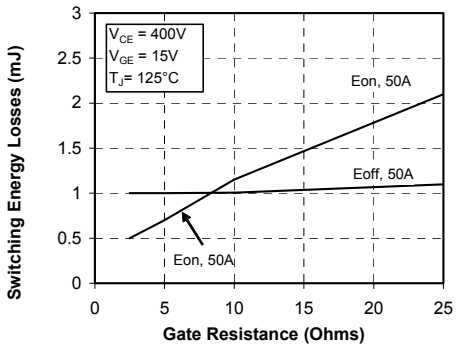
Turn-On Energy Loss vs Collector Current



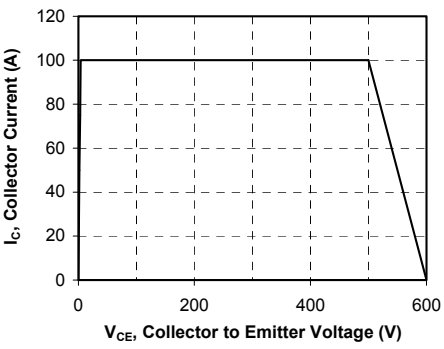
Turn-Off Energy Loss vs Collector Current

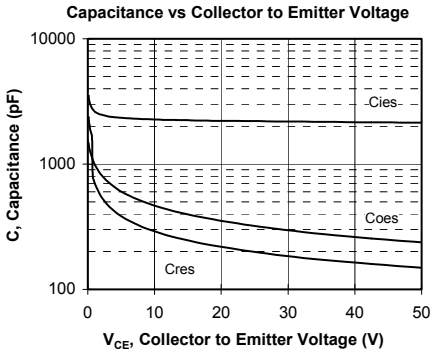


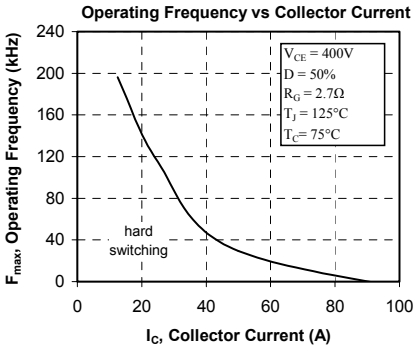
Switching Energy Losses vs Gate Resistance

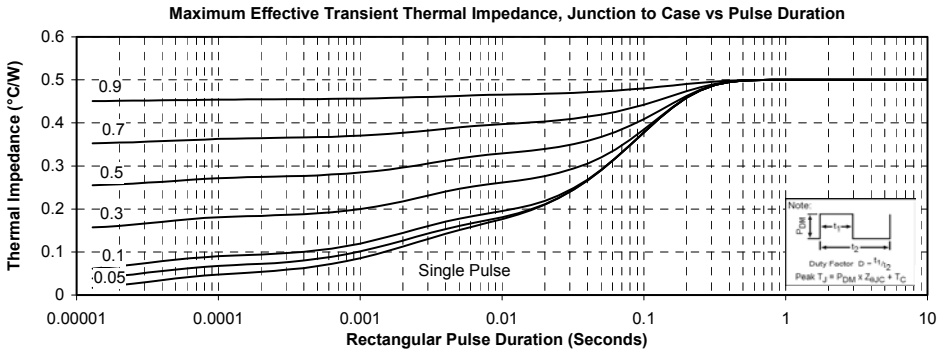


Reverse Bias Safe Operating Area









Microsemi reserves the right to change, without notice, the specifications and information contained herein